Amendments to the Specification:

Please replace the Abstract on page 71, with the following rewritten paragraph:

ABSTRACT

In a stacked-layer type photoelectric conversion device, a plurality of photoelectric conversion units ~~(3; 5)~~ are stacked on a substrate ~~(1)~~, each of which includes a one conductivity-type layer ~~(31; 51)~~, a photoelectric conversion layer ~~(32; 52)~~ of substantially intrinsic semiconductor and an opposite conductivity-type layer ~~(33; 53)~~ in this order from a light-incident side. At least one of the opposite conductivity-type layer ~~(33)~~ in a front photoelectric conversion unit ~~(3)~~ arranged relatively closer to the light-incident side and the one conductivity-type layer ~~(51)~~ in a back photoelectric conversion unit ~~(5)~~ arranged adjacent to the front photoelectric conversion unit ~~(3)~~ includes a silicon composite layer ~~(4)~~ at least in a part thereof. The silicon composite layer ~~(4)~~ has a thickness of more than 20 nm and less than 130 nm and an oxygen concentration of more than 25 atomic % and less than 60 atomic %, and includes silicon-rich phase parts in an amorphous alloy phase of silicon and oxygen.